

MG30G2CL3

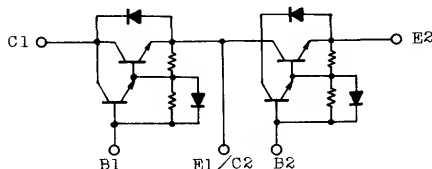
SILICON NPN TRIPLE DIFFUSED TYPE
(DARLINGTON POWER MODULE)

HIGH POWER SWITCHING APPLICATIONS.
MOTOR CONTROL APPLICATIONS.

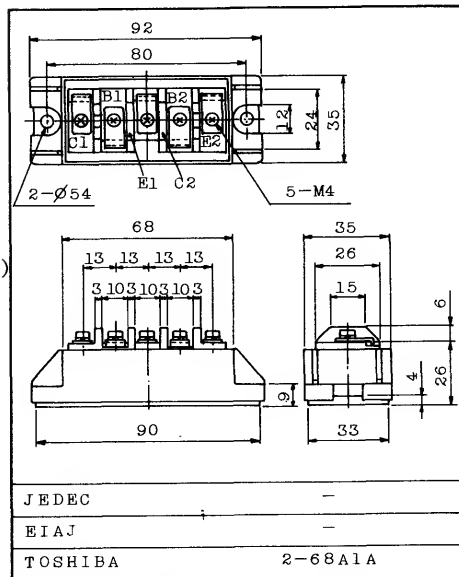
FEATURES:

- . The Collector is Isolated from Case.
- . 2 Power Transistor and 2 Free Wheeling Diodes are Built-in to 1 Package.
- . High DC Current Gain : $h_{FE}=100(\text{Min.})$ ($I_C=30A$)
- . Low Saturation Voltage : $V_{CE}(\text{sat})=2V(\text{Max.})$ ($I_C=30A$)
- . High Speed : $t_f=2\mu s(\text{Max.})$ ($I_C=30A$)

EQUIVALENT CIRCUIT



Unit in mm

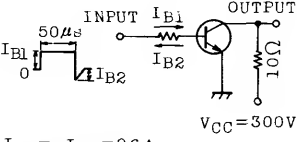


Weight : 210g

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CB0}	600	V
Collector- Emitter Voltage		V_{CE0}	600	V
Collector-Emitter Sustaining Voltage		$V_{CE0}(\text{SUS})$	450	V
Emitter-Base Voltage		V_{EB0}	6	V
Collector Current	DC	I_C	30	A
	1ms	I_C	60	A
	DC	$-I_C$	30	A
Base Current		I_B	2.0	A
Collector Power Dissipation ($T_c=25^\circ\text{C}$)		P_C	250	W
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-40 ~ 125	$^\circ\text{C}$
Isolation Voltage		V_{isol}	2000 (AC 1 Minute)	V
Screw Torque (Terminal/Mounting)			20/30	kg·cm

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} =600V, I _E =0	-	-	1.0	mA
Emitter Cut-off Current		IEBO	VEB=6V, I _C =0	-	-	200	mA
Collector-Emitter Sustaining Voltage		V _{CEO(SUS)}	I _C =0.5A, L=40mH	450	-	-	V
DC Current Gain		h _{FE}	V _{CE} =5V, I _C =30A	100	-	-	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =30A, I _B =0.6A	-	-	2.0	V
Base-Emitter Saturation Voltage		V _{BE(sat)}		-	-	2.5	V
Emitter-Collector Voltage		VECO	I _E =30A, I _B =0	-	-	1.5	V
Reverse Recovery Time		t _{rr}	-I _C =30A, V _{EB} =3V V _{CE} =300V	-	-	2.0	μs
Collector Output Capacitance		C _{ob}	V _{CB} =50V, I _E =0, f=1MHz	-	350	-	pF
Switching Time	Turn-on Time	t _{on}	 INPUT I_{B1} 50μs I_{B2} OUTPUT 10Ω V_{CE}=300V I_{B1}=-I_{B2}=0.6A DUTY CYCLE=0.5%	-	-	1.0	μs
	Storage Time	t _{stg}		-	-	12	
	Fall Time	t _f		-	-	2.0	
Thermal Resistance (Junction to Case)		R _{th(j-c)}	Transistor	-	-	0.5	°C/W
			Diode	-	-	1.8	

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